

Application No. 10/718,102

IN THE CLAIMS

1. (Currently Amended) A method comprising:
providing a coating over a wafer;
testing a semiconductor tool using the coated wafer; and
replacing at least a portion of the coating of the wafer with
a layer of coating, wherein each coating comprises at least one
characteristic of a single crystal structure.
- 2-5. (Cancelled)
6. (Original) The method of Claim 1, further comprising
testing surface contaminant adding properties of the semiconductor
tool.
7. (Currently Amended) The method of Claim 6, wherein the
testing surface contaminant adding properties comprises testing light
scattering properties of a surface of the coating of the wafer.
8. (Previously Presented) The method of Claim 1, wherein the
at least one characteristic of a single crystal structure comprises
insignificant distortion of an angle of refraction of incident light.
- 9-22. (Cancelled)
23. (Currently Amended) The method of Claim 1, wherein the
providing a coating comprises:
providing a polysilicon layer over the wafer; and
surface polishing the polysilicon layer.

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24. (Currently Amended) The method of Claim 1, wherein the replacing comprises:

mechanically grinding a portion of the coating;
providing a polysilicon layer over a portion of the wafer where the coating was removed by grinding; and
surface polishing the polysilicon layer.

25. (Currently Amended) The method of Claim 1, further comprising removing contaminants from a surface of the coating of the wafer used to test the semiconductor tool.

26. (Previously Presented) A method comprising:
replacing at least a portion of a coating of a wafer with a layer of coating, wherein each coating has at least one characteristic of a single crystal structure; and
testing at least one characteristic of a semiconductor tool using the coated wafer.

27. (Previously Presented) The method of Claim 26, wherein the replacing comprises:

mechanically grinding the coating of the wafer;
providing a polysilicon layer over a portion of the wafer where the coating was removed by grinding; and
surface polishing the polysilicon layer.

28. (Previously Presented) The method of Claim 27, wherein the replacing further comprises removing contaminants from a surface of the coating of the wafer.

29-32. (Cancelled)

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33. (Previously Presented) The method of Claim 26, further comprising testing surface contaminant adding properties of the semiconductor tool.

34. (Currently Amended) The method of Claim 33, wherein the testing surface contaminant adding properties comprises testing light scattering properties of a surface of the coating of the wafer.

35. (Previously Presented) The method of Claim 26, wherein the at least one characteristic of a single crystal structure comprises insignificant distortion of an angle of refraction of incident light.